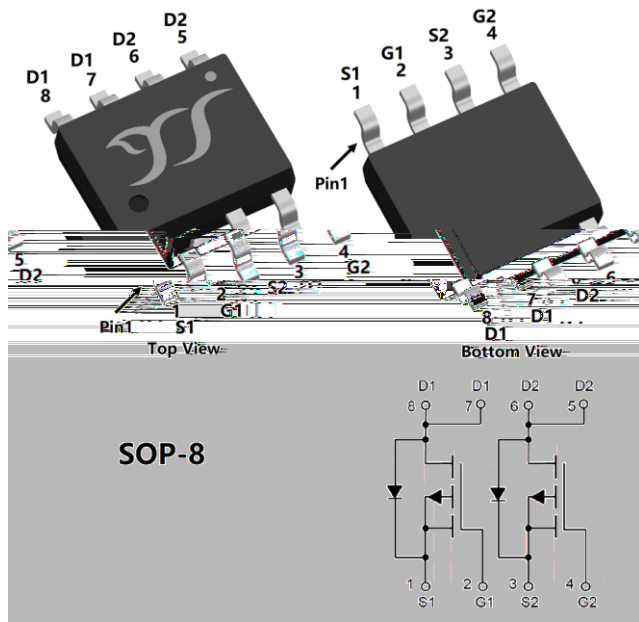


## P-Channel and P-Channel Complementary MOSFET



### Product Summary

$V_{DS}$	-30 V
$I_D$	-10 A
$R_{DS(ON)}$ ( at $V_{GS}=-10V$ )	<20 m
$R_{DS(ON)}$ ( at $V_{GS}=-4.5V$ )	<28 m
100% EAS Tested	

### General Description

Trench Power LV MOSFET technology  
 High density cell design for Low RDS(ON)  
 High Speed switching  
 : Va R R W W 9R RY  
 Epoxy Meets UL 94 V-0 Flammability Rating  
 Halogen Free

### Applications

Battery protection  
 Load switch  
 Power management

### Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		$V_{DS}$	-30	V
Gate-source Voltage		$V_{GS}$	$\pm 20$	V
Drain Current	$T_A=25$	$I_D$	-10	A
	$T_A=100$		-6.3	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	-80	A
Avalanche energy <sup>B</sup>		EAS	49	mJ
Total Power Dissipation <sup>C</sup>	$T_A=25$	$P_D$	2.5	W
	$T_A=100$		1	
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~+150	

### Thermal resistance

Parameter	Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient <sup>D</sup>	$R_{\theta J}$	40	50	/W

### Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJS7328B	F2	Q7328B	4000	8000	64000	13 reel



# YJS7328B

## Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =-	-30	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	-	-	-1	-
		V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V, T <sub>J</sub> =150	-	-	-100	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> =0V	-	-	±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =-	-1	-1.5	-2.5	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-10A	-	15	20	Z
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-5A	-	21	28	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-10A, V <sub>GS</sub> =0V	-	-0.9	-1.3	V
Gate resistance	R <sub>G</sub>	f=1MHz	-	16	-	
Maximum Body-Diode Continuous Current	I <sub>S</sub>		-	-	-10	A
<b>Dynamic Parameters</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHz	-	1220	-	pF
Output Capacitance	C <sub>oss</sub>		-	170	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	160	-	
<b>Switching Parameters</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-10A	-	24	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	2	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	6	-	
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =-10A, di/dt=100A/us	-	11	-	nC
Reverse Recovery Time	t <sub>rr</sub>		-	35	-	ns
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =-10V, V <sub>DD</sub> =-15V, I <sub>D</sub> =-10A R <sub>GEN</sub> =2.5	-	11	-	ns
Turn-on Rise Time	t <sub>r</sub>		-	4	-	
Turn-off Delay Time	t <sub>D(off)</sub>		-	70	-	
Turn-off fall Time	t <sub>f</sub>		-	50	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. T<sub>J</sub>=25 , V<sub>DD</sub>=-30V, V<sub>G</sub>=-10V, R<sub>G</sub> 9 0.5mH, I<sub>AS</sub>=-14A.

C. P<sub>d</sub> is based on max. junction temperature, using junction-case and junction-ambient thermal resistance.

D. The value of R<sub>θ</sub> is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in the still air environment with T<sub>A</sub> =25 .  
The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.



■ Typical Electrical and Thermal Characteristics Diagrams

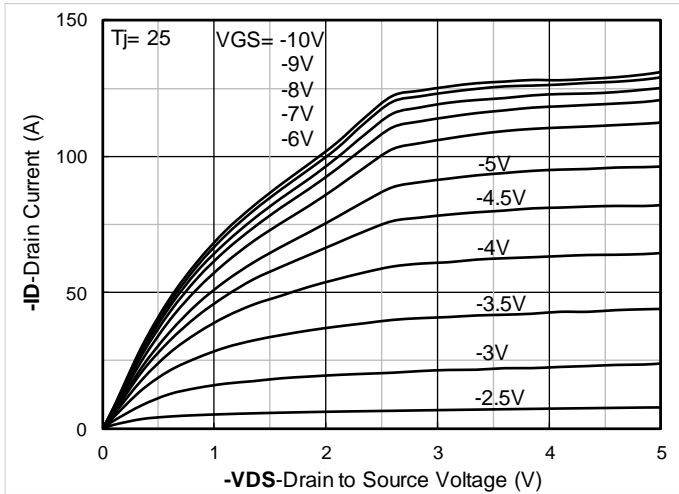


Figure 1. Output Characteristics

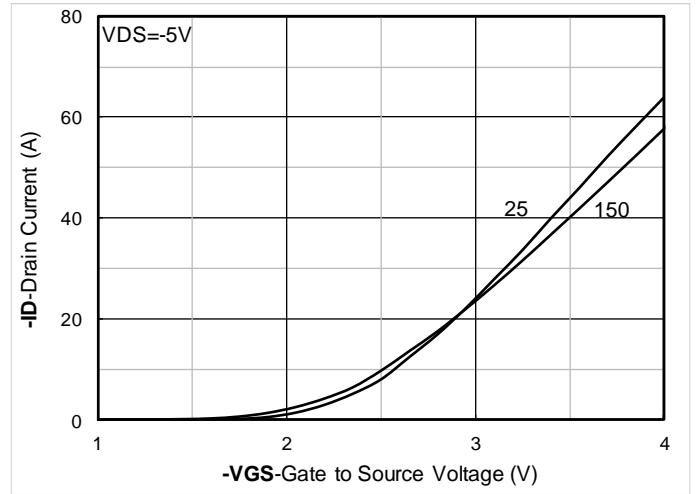


Figure 2. Transfer Characteristics

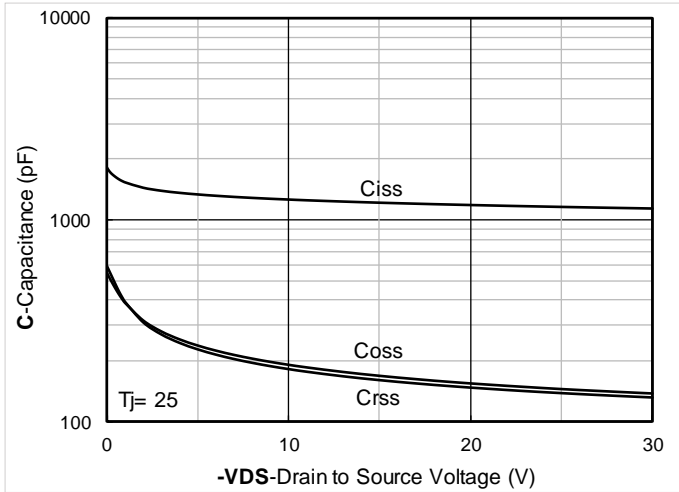


Figure 3. Capacitance Characteristics

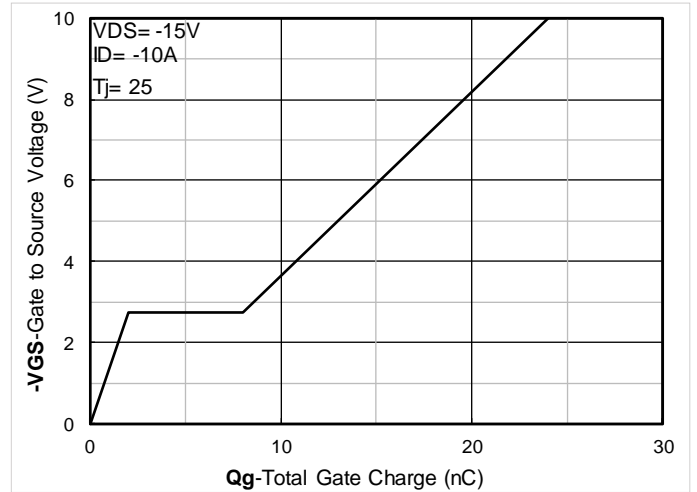


Figure 4. Gate Charge

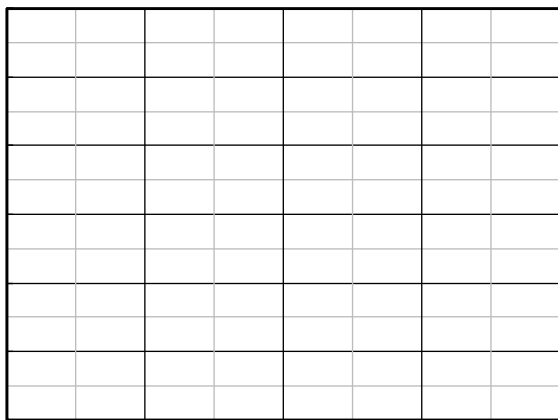


Figure 5. On-Resistance vs Gate to Source Voltage

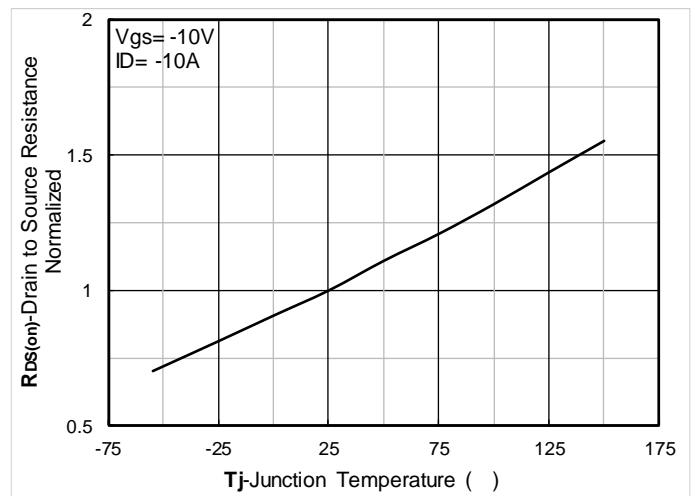


Figure 6. Normalized On-Resistance

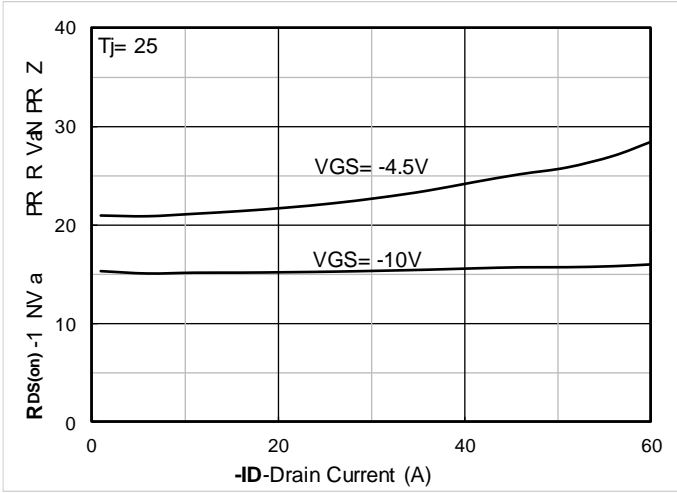


Figure 7. RDS(on) VS Drain Current

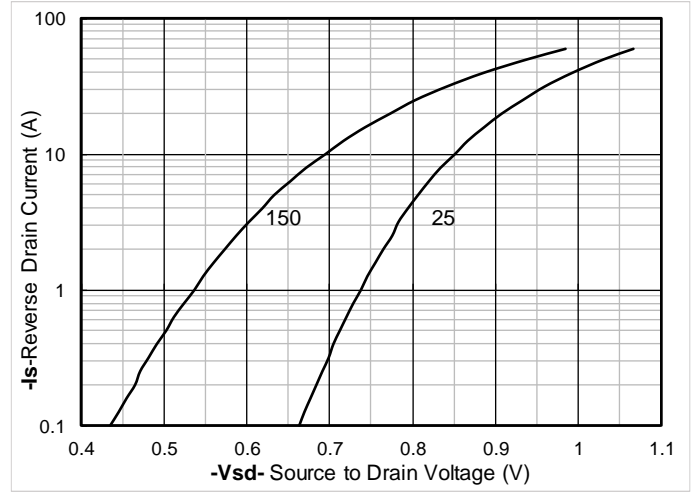


Figure 8. Forward characteristics of reverse diode

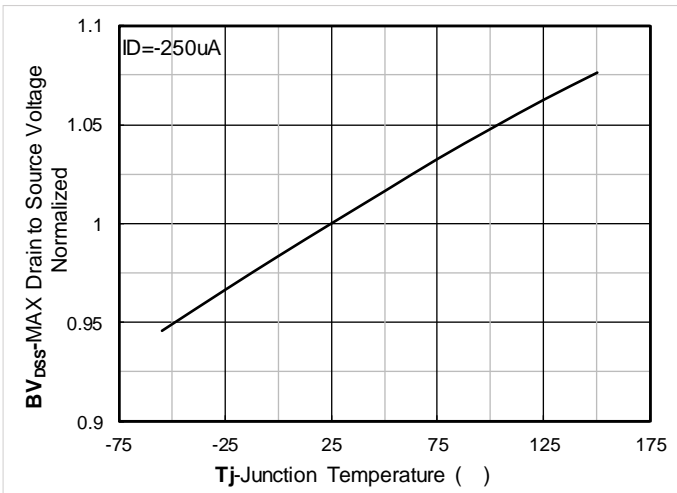


Figure 9. Normalized breakdown voltage

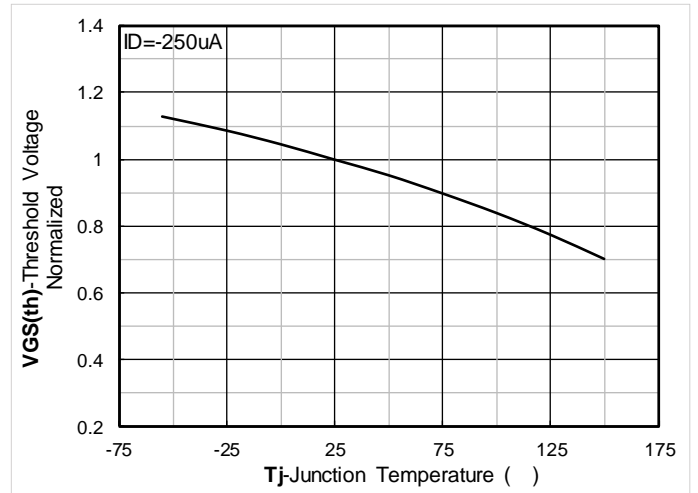


Figure 10. Normalized Threshold voltage

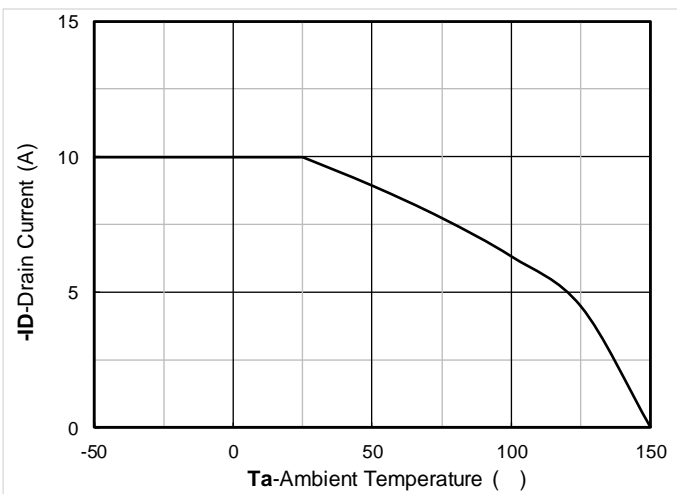


Figure 11. Current dissipation

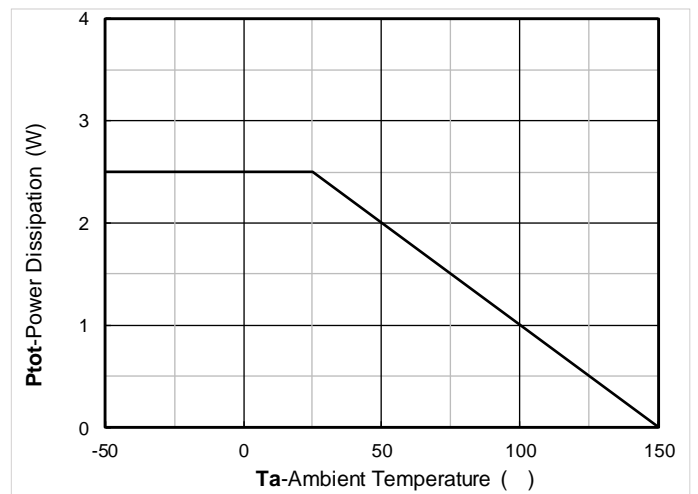


Figure 12. Power dissipation

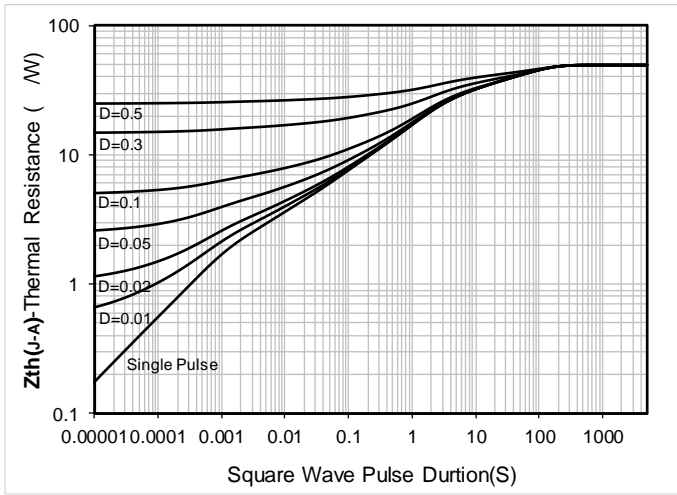


Figure 13. Maximum Transient Thermal Impedance

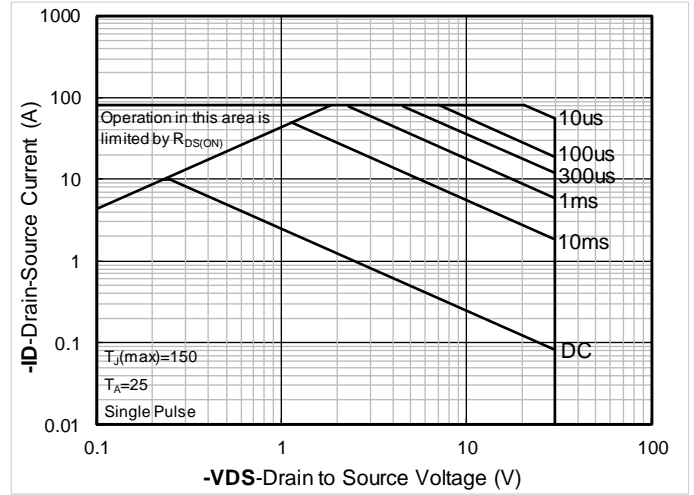
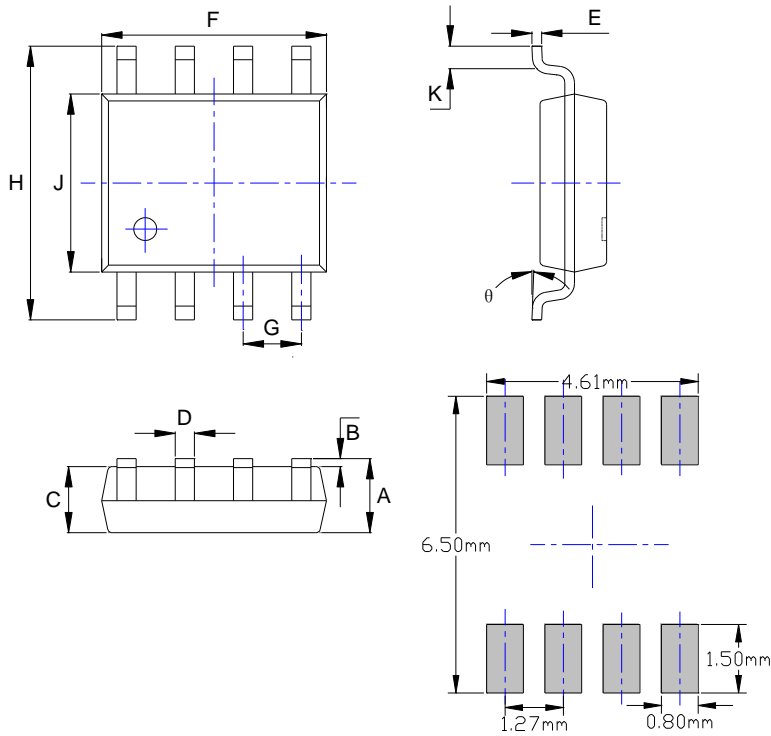


Figure 14. Safe Operation Area

## SOP-8 Package information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.053	0.069	1.350	1.750
B	0.004	0.010	0.100	0.250
C	0.053	0.061	1.350	1.550
D	0.013	0.020	0.330	0.510
E	0.007	0.010	0.170	0.250
F	0.189	0.197	4.800	5.000
G	0.050BSC		1.270BSC	
H	0.228	0.244	5.800	6.200
J	0.150	0.157	3.800	4.000
K	0.016	0.050	0.400	1.270
$\theta$	0°	8°	0°	8°

**Note:**

1. Controlling dimension: in millimeters.
2. General tolerance: +/-0.05mm.
3. The pad layout is for reference purposes only.



## YJS7328B

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